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Kind regards,

Team Nexperia



BAS101; BAS101S High-voltage switching diodes Rev. 02 — 14 December 2009

Product data sheet

Product profile 1.

1.1 General description

High-voltage switching diodes, encapsulated in a SOT23 small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
BAS101	SOT23	-	single
BAS101S	SOT23	-	dual series

1.2 Features

- High switching speed: $t_{rr} \le 50$ ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \le 300 \text{ V}$
- Low capacitance: C_d ≤ 2 pF
- Reverse voltage: V_R ≤ 300 V
- Small SMD plastic package

1.3 Applications

- High-speed switching
- High-voltage switching
- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I _F	forward current		-	-	200	mA
I _R	reverse current	$V_{R} = 250 \text{ V}$	-	-	150	nA
V_R	reverse voltage		-	-	300	V
t _{rr}	reverse recovery time		<u>[1]</u> -	-	50	ns

[1] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA.



2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
BAS101			
1	anode		_
2	not connected	3	3
3	cathode	1 2	1 + 2 006aaa764
BAS101S			
1	anode (diode 1)		
2	cathode (diode 2)	3	3
3	cathode (diode 1), anode (diode 2)	1 2	1 2 006aaa763

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
BAS101	-	plastic surface-mounted package; 3 leads	SOT23		
BAS101S					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BAS101	*HQ
BAS101S	*HR

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_{RRM}	repetitive peak reverse		-	300	V
	voltage	series connection	-	600	V
V_R	reverse voltage		-	300	V
		series connection	-	600	V
l _F	forward current		-	200	mΑ
		series connection	-	100	mΑ
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	1	Α
I _{FSM}	non-repetitive peak forward current	square wave; $t_p \le 1 \mu s$	[1] -	9	Α
Per device)				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2] _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] $T_i = 25$ °C prior to surge

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

7. Characteristics

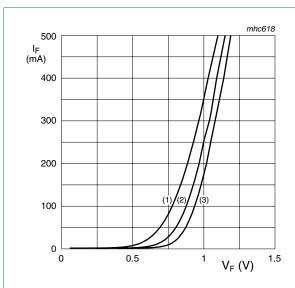
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Tamb = 20 0 amos out of which							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
V _F	forward voltage	I _F = 100 mA	[1]	-	-	1.1	V
I _R	reverse current	V _R = 250 V		-	-	150	nA
		V _R = 250 V; T _j = 150 °C		-	-	100	μΑ
C _d	diode capacitance	$V_R = 0 V$; $f = 1 MHz$		-	-	2	pF
t _{rr}	reverse recovery time		[2]	-	-	50	ns

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA.



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 75 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values

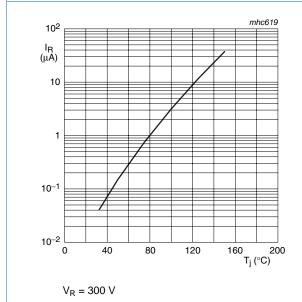
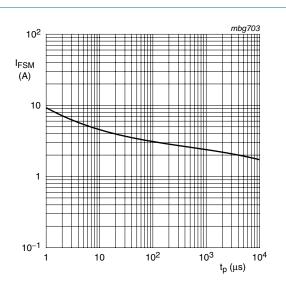
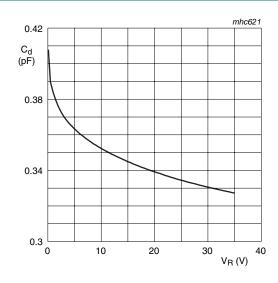


Fig 3. Reverse current as a function of junction temperature; typical values



Based on square wave currents $T_i = 25$ °C; prior to surge

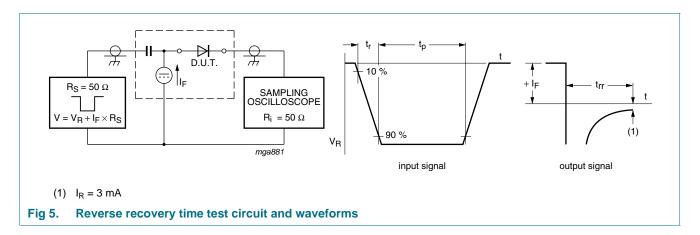
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



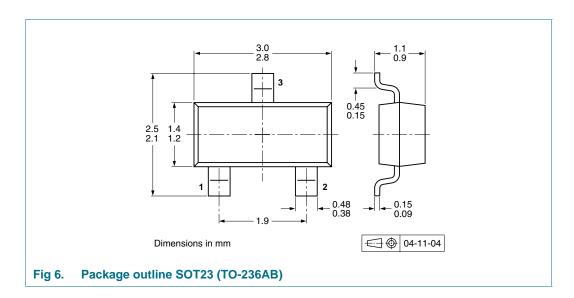
 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

8. Test information



9. Package outline



10. Packing information

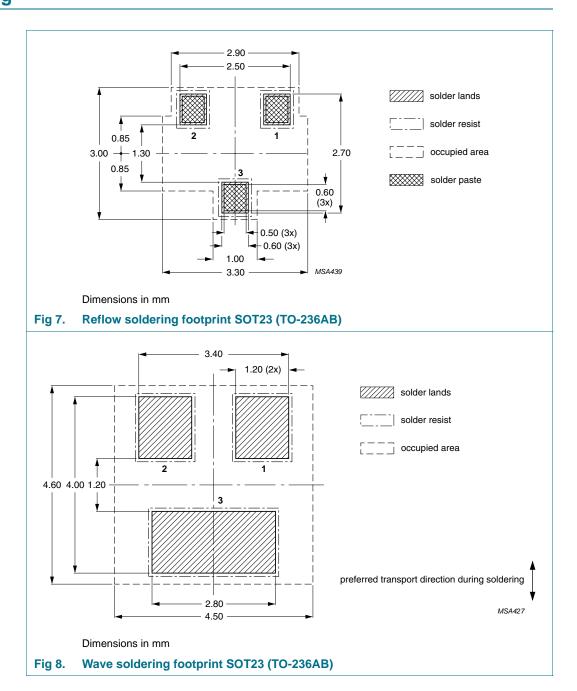
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

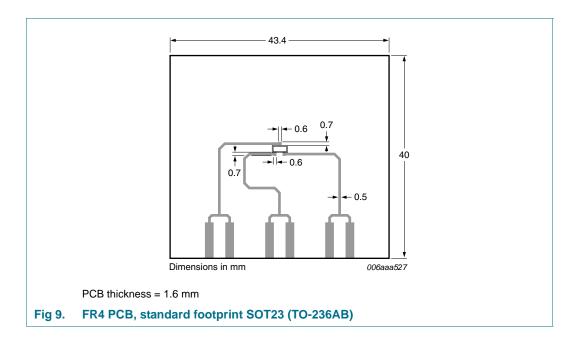
Type number	Package	Description	Packing quantity	
			3000	10000
BAS101	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
BAS101S				

[1] For further information and the availability of packing methods, see <u>Section 15</u>.

11. Soldering



12. Mounting



BAS101; BAS101S

High-voltage switching diodes

13. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS101_BAS101S_2	20091214	Product data sheet	-	BAS101_BAS101S_1
Modifications:		eet was changed to reflect w legal definitions and disconing": updated		
BAS101_BAS101S_1	20060908	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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BAS101; BAS101S

High-voltage switching diodes

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